Title (en)

METHOD AND DEVICE FOR CONTACTING SEMICONDUCTOR CHIPS

Title (de)

VERFAHREN UND VORRICHTUNG ZUM KONTAKTIEREN VON HALBLEITERCHIPS AUF EINEM METALLISCHEN SUBSTRAT

Title (fr)

PROCEDE ET DISPOSITIF DE CONNEXION DE PUCES DE SEMI-CONDUCTEUR

Publication

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Application

EP 04762724 A 20040828

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Abstract (en)

[origin: WO2005027200A2] The invention relates to a method and device that make it possible to increase the productivity of the chip bonding and the before and after working steps associated with the chip bonding. To this end, the invention provides a method for contacting semiconductor chips (3) on a metallic substrate (16), whereby an etch resist (27) is located at least on one substrate side, and semiconductor chips (3) are contacted on the contacting side (30) by means of flip-chip bonding processes, during which a contacting region (7) is created on the contacting side (30) of the substrate (16). A semiconductor chip (3) having two contact bumps (6) is contacted on said contacting region in such a manner that: a contact bump (6) is contacted on both sides of a structure line (35) or of a structure trench (13) dividing the contacting region (7), and; after the contacting, an underfilling of the chip (3) ensues after which an electrically insulating passage (14) is made in the contacting region (7), and a module (32), which supports the semiconductor chip (3), is removed from the substrate (16).

IPC 1-7

H01L 21/00

IPC 8 full level

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